NSN 5961-01-301-4831

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View Online at https://aerobasegroup.com/nsn/5961-01-301-4831 **Inclosure Material:** Metal **Overall Length:** 1.646 inches Overall Diameter: 0.650 inches **End Application:** 5895-01-269-3572 an/mpn-14k landing control central; an/spn-43b, 43c; forrestal class cv; nimitz class cvn; simulator an/mpq-t3 **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-48 **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Overall Width Across Flats:** Between 0.544 inches and 0.562 inches **Thread Size:** 0.250 inches **Criticality Code Justification:** Feat **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 1200.0 nonrepetitive peak reverse voltage and 1000.0 repetitive peak reverse voltage and 1000.0 repetitive peak off-state voltage **Current Rating Per Characteristic:** 2.00 milliamperes forward current, average of standard range and 2.00 milliamperes forward current, average nanoamperes **Power Rating Per Characteristic:** 60.0 watts small-signal input power, common-collector not applicable **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Weapon system essential **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug Shelf Life: N/a

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Unit Of Measure:

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Demilitarization:

No

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